



STP90NF03L STB90NF03L-1

N-CHANNEL 30V - 0.0056Ω - 90A TO-220/I²PAK
LOW GATE CHARGE STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP90NF03L	30 V	< 0.0065 Ω	90 A
STB90NF03L-1	30 V	< 0.0065 Ω	90 A

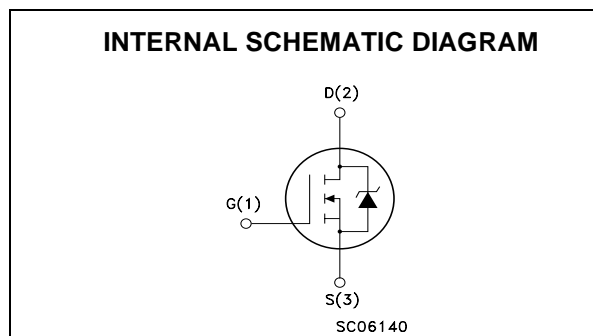
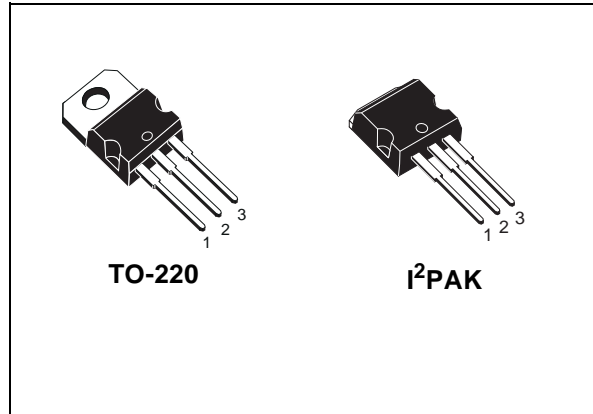
- TYPICAL R_{DS(on)} = 0.0056 Ω
- TYPICAL Q_g = 35 nC @ 5V
- OPTIMAL R_{DS(on)} x Q_g TRADE-OFF
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED

DESCRIPTION

This application specific Power Mosfet is the third generation of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows the best trade-off between on-resistance and gate charge. When used as high and low side in buck regulators, it gives the best performance in terms of both conduction and switching losses. This is extremely important for motherboards where fast switching and high efficiency are of paramount importance.

APPLICATIONS

- SPECIFICALLY DESIGNED AND OPTIMISED FOR HIGH EFFICIENCY CPU CORE DC/DC CONVERTERS



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP90NF03L	P90NF03L	TO-220	TUBE
STB90NF03L-1	B90NF03L	I ² PAK	TUBE

STP90NF03L/STB90NF03L-1

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate- source Voltage	±20	V
I _D	Drain Current (continuous) at T _C = 25°C	90	A
I _D	Drain Current (continuous) at T _C = 100°C	65	A
I _{DM} (●)	Drain Current (pulsed)	360	A
P _{TOT}	Total Dissipation at T _C = 25°C	150	W
	Derating Factor	0.73	W/°C
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case Max	1	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300	°C

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED) ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} , V _{GS} = 10V	90			A
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1		2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 45 A V _{GS} = 5V, I _D = 45 A		0.0056 0.007	0.0065 0.012	Ω Ω

ELECTRICAL CHARACTERISTICS (CONTINUED)
DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 45 \text{ A}$		40		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $f = 1 \text{ MHz}$, $V_{GS} = 0$		2700		pF
C_{oss}	Output Capacitance			860		pF
C_{rss}	Reverse Transfer Capacitance			170		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{V}$, $I_D = 45 \text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 4.5 \text{ V}$ (see test circuit, Figure 3)		30		ns
t_r	Rise Time			200		ns
Q_g	Total Gate Charge	$V_{DD} = 24\text{V}$, $I_D = 90 \text{ A}$, $V_{GS} = 5\text{V}$		35	47	nC
Q_{gs}	Gate-Source Charge			10		nC
Q_{gd}	Gate-Drain Charge			18		nC

SWITCHING OFF

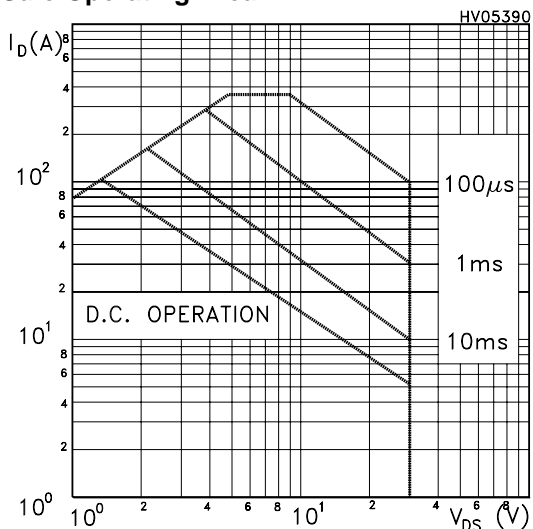
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 15\text{V}$, $I_D = 45 \text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 4.5 \text{ V}$ (see test circuit, Figure 3)		50		ns
t_f	Fall Time			105		ns

SOURCE DRAIN DIODE

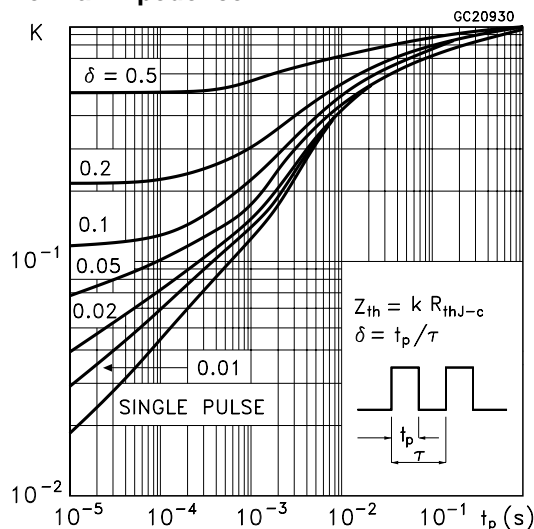
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				90	A
I_{SDM} (2)	Source-drain Current (pulsed)				360	A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 90 \text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 90 \text{ A}$, $di/dt = 100\text{A}/\mu\text{s}$, $V_{DD} = 15\text{V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		80		ns
Q_{rr}	Reverse Recovery Charge			90		nC
I_{RRM}	Reverse Recovery Current			2.5		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

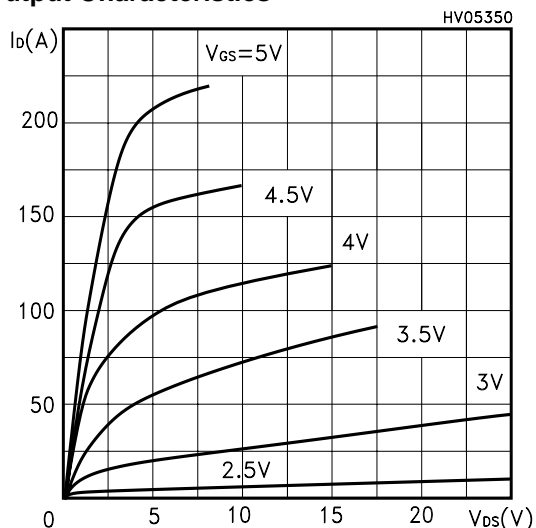
Safe Operating Area



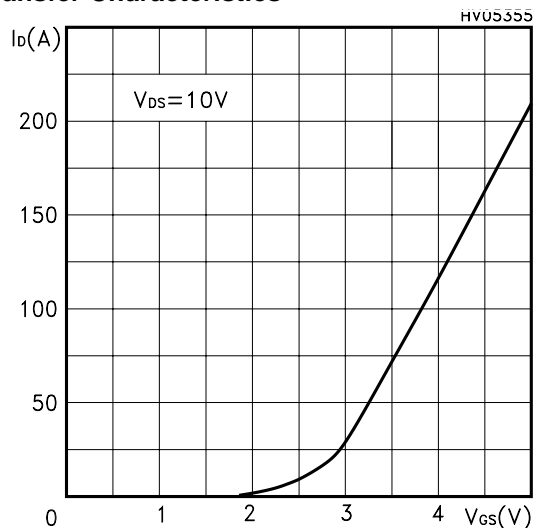
Thermal Impedance



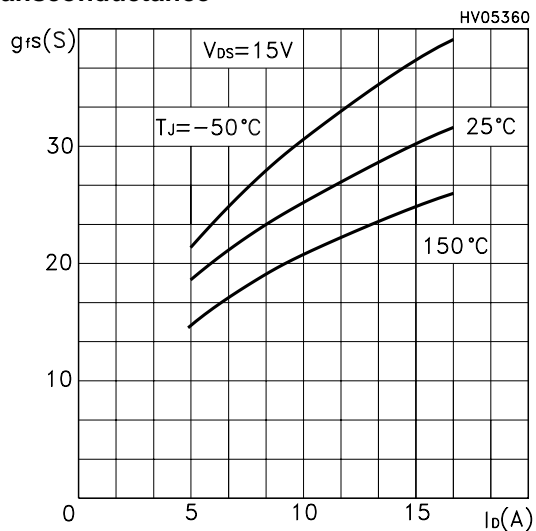
Output Characteristics



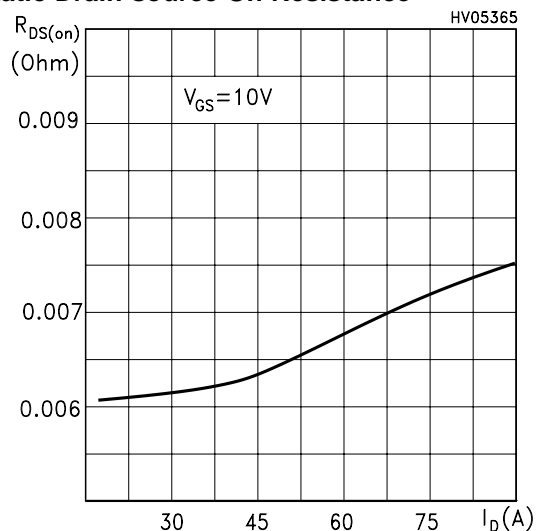
Transfer Characteristics



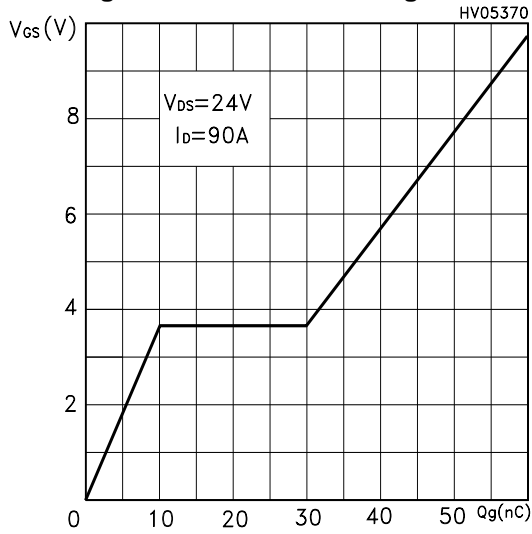
Transconductance



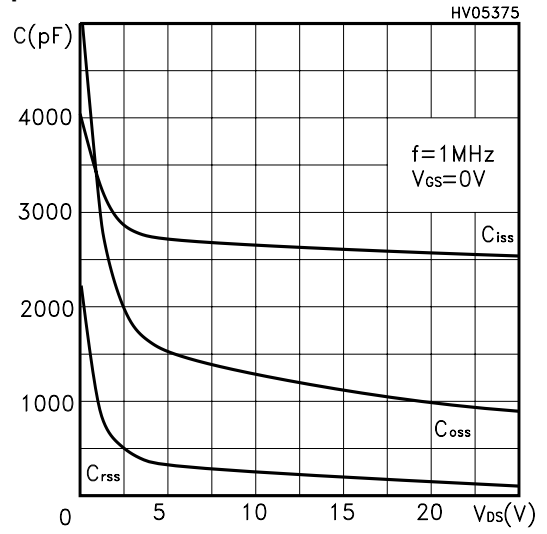
Static Drain-source On Resistance



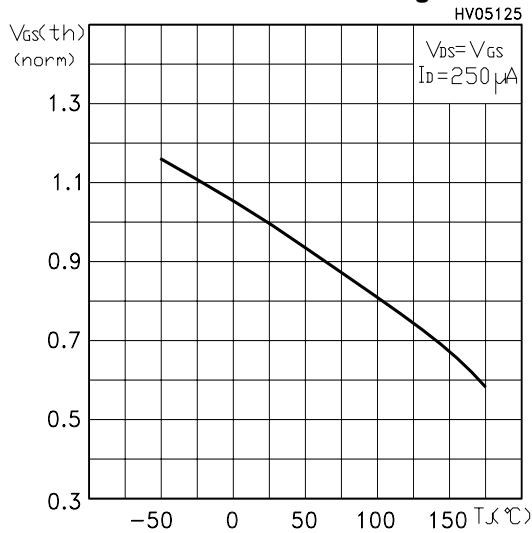
Gate Charge vs Gate-source Voltage



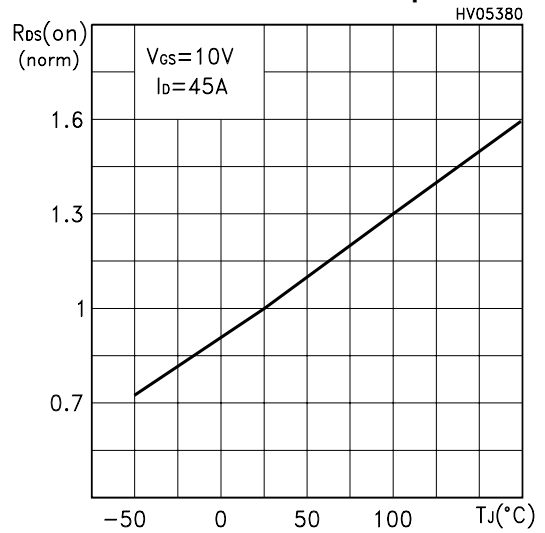
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

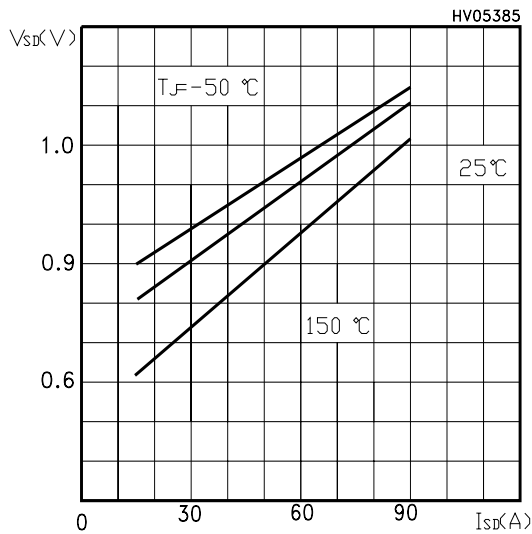


Fig. 1: Unclamped Inductive Load Test Circuit

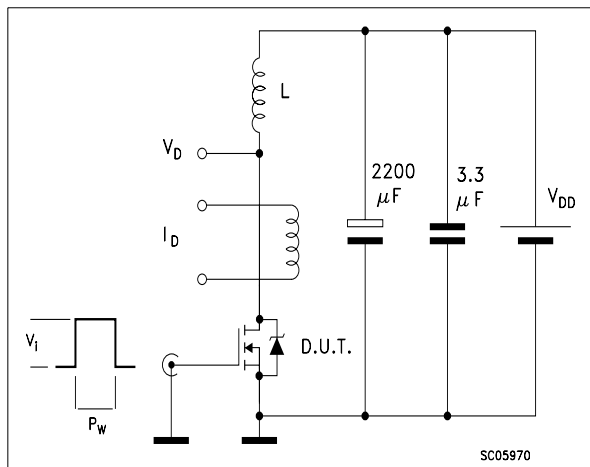


Fig. 2: Unclamped Inductive Waveform

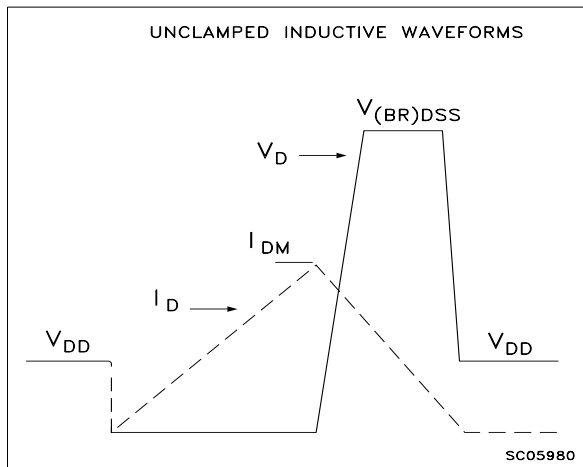


Fig. 3: Switching Times Test Circuit For Resistive Load

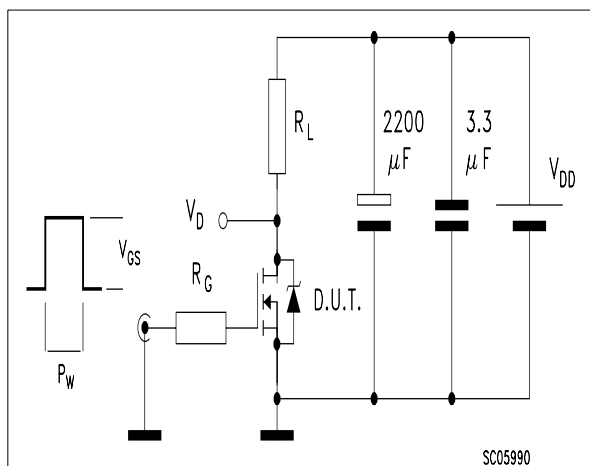


Fig. 4: Gate Charge test Circuit

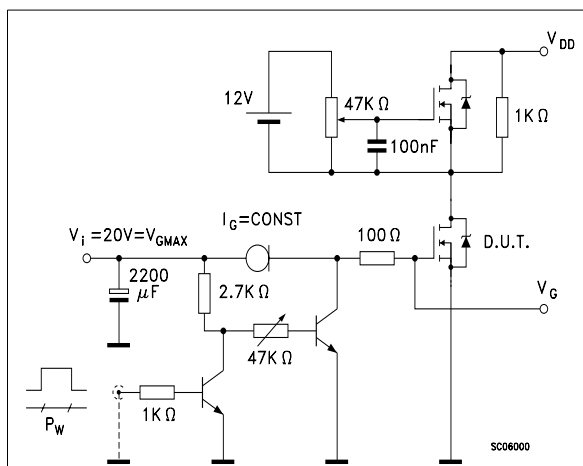
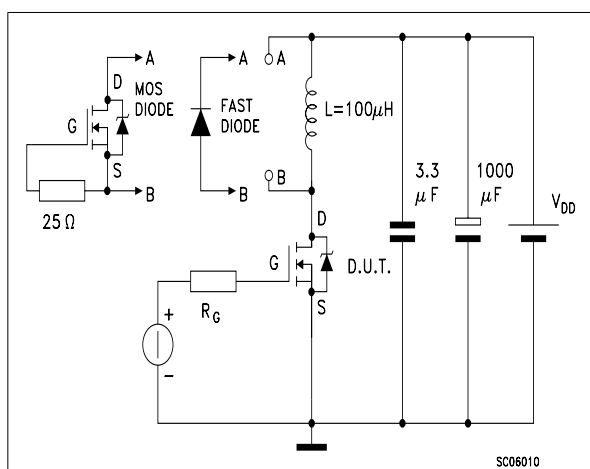
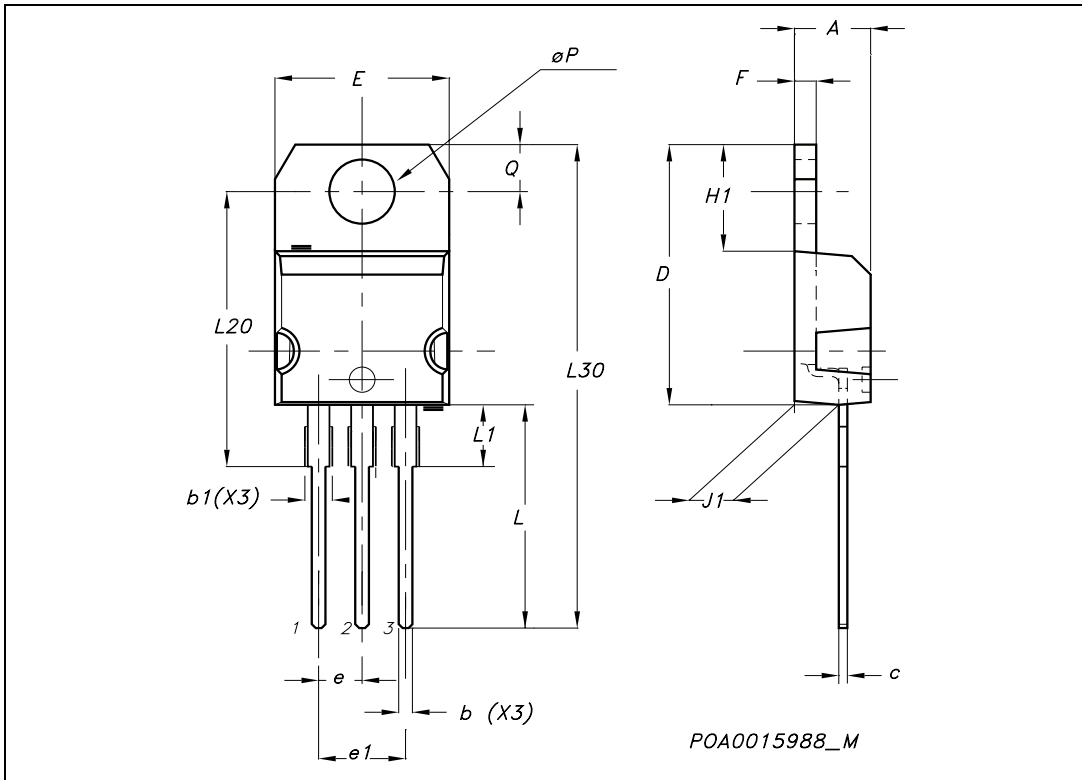


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



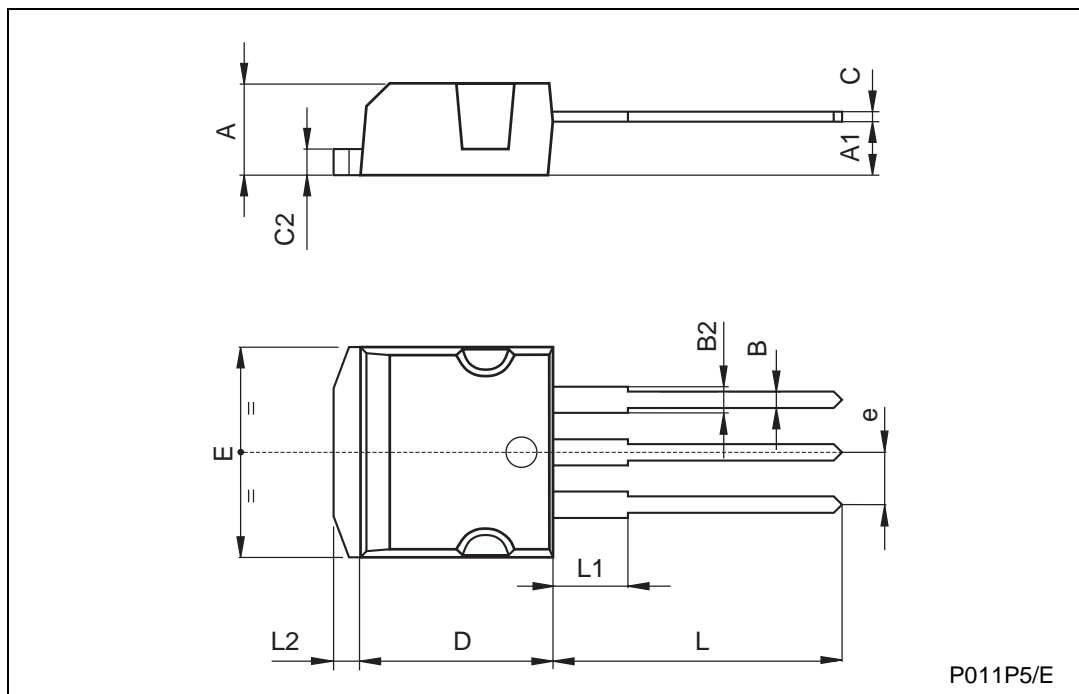
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055



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